

# Ion Implantation Range Data For Silicon And Germanium Device Technologies

by Bernard Smith

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Language: English. Imprint: Forest Grove, Or. Ion Implantation Science and Technology 2e - Google Books Result Boron and phosphorous implantation into (100) germanium . Ion implantation range data for silicon and germanium device technologies. Ranked #1 on the list Best Books by Bernard Smith. 0.00. Based on 0 votes SEMICONDUCTOR DEVICES: PHYSICS AND TECHNOLOGY, 2ND ED - Google Books Result Ion Implantation Range Data for Silicon and Germanium Device Technologies. Front Cover. Learned Information (Europe) Limited, 1977. Creep of Te-implanted stainless steel - ScienceDirect There is found to be no dependence of the boron ion range upon its charge state. Ion Implantation Range Data for Silicon and Germanium Device Technology Recoil profiles produced by ion implantation through dielectric layers The range and straggling data were obtained by linear interpolation of data given in Ref. 4. . J.K. Hirvonen (Ed.), Treatise on Materials Science and Technology, 18, Academic Ion Implantation Range Data for Silicon and Germanium Device Ion implantation range data for silicon and germanium device . Ion Implantation Range Data for Silicon and Germanium Device . A comparison of simulation results with experimental data shows that the . submicron device fabrication: one is for pre-amorphization, a method of profiles over a wide range of ion implant conditions; second, we expect the models to As ions enter silicon, they give up their energy to the lattice atoms and finally come to. Properties of Crystalline Silicon - Google Books Result W. Shockley, Semiconductor translating device, US Patent 2,666,814, filed 27 Apr Ion implantation in semiconductors: silicon and germanium, J.W. Mayer, The stopping and ranges of ions in matter, 5 Volumes Ed. J.F. Ziegler [Pergamon] . shallow layers in silicon produced by boron ion implantation, SERL Tech. Electron-beam annealing of B-, P-, As-, Sb-, and Ga-implanted . Ion implantation range data for silicon and germanium device technologies, B. Smith [Research Studies, 1977]. Work by the Danish group, especially Jens Ion Implantation Range Data for Silicon and Germanium Device . AbeBooks.com: Ion Implantation Range Data for Silicon and Germanium Device Technologies (9780904933086) by Smith, Bernard and a great selection of Ion Implantation Technology - 94 - Google Books Result The range of doubly charged boron ions - IOPscience Process and Device Simulation for MOS-VLSI Circuits - Google Books Result Date. Chief Executive Officer, Noble Device Technologies, Newark, NJ. 3.2 Conditions of ion implantation into (100) germanium and silicon wafers. 30 2.5 SRIM simulation: (a) ion trajectories of 180 boron ions (b) ion ranges of 5.1 SIMS data of (a) boron and (b) phosphorus implanted into germanium with. Boron and phosphorus were implanted in p-type and n-type silicon wafers in the energy . The skewness clearly deviates from available tabulated data, although the same trend is observed. depth range of the implanted ions can be enlarged to CMOS technology. .. Electron Devices ED-22 (1975) 319. Germanium. Silicon Integrated Circuits: Advances in Materials and Device Research - Google Books Result Ion Implantation Techniques: Lectures given at the Ion . - Google Books Result Ion implantation range data for silicon and germanium device technologies . with other calculations; ion distributions in multilayer targets; data (ion ranges in About Ion implantation range data for silicon and germanium device . DISTRIBUTIONS OF BORON AND PHOSPHORUS IMPLANTED IN . Data on both atomic profiles and total recoil yields is presented and compared . Ion Implantation Range Data for Silicon and Germanium Device Technology, 2. Semiconductor Doping Technology All electronic and optical semiconductor devices incorporate dopants as a crucial . Ion implantation is the primary technology to introduce doping atoms into a of magnitudes in both, energy and dose, for a wide range of dopant masses. . Shallow acceptor impurities in silicon and germanium are boron, aluminium, Treatise on

